

REMARKS

Claims 20, 28-31, 33-45, 47-53, 55 and 56 are pending in this application, with claims 20, 34, 41 and 49 being independent. Claims 41 and 49 have each been amended to recite that a part of the first layer and a part of the second layer are located over the interlayer insulating film. Claim 49 has additionally been amended to recite that a part of the third layer and a part of the fourth layer are located over the interlayer insulating film. Support for these amendments may be found in the application at, for example, Fig. 3C. No new matter has been introduced.

Independent claims 20, 34, 41 and 49, and their dependent claims 28, 31, 35, 38, 42, 45, 47, 50, 53 and 55, have been rejected as being anticipated by Kudoh (U.S. Patent No. 5,159,416). Each of independent claims 20, 34, 41 and 49 recites, among other features, a semiconductor layer on an insulating surface, wherein the semiconductor layer has a side recess. Applicants request reconsideration and withdrawal of the rejection of claims 20, 34, 41 and 49, and their dependent claims, because Kudoh does not describe or suggest the semiconductor layer having a side recess.

Kudoh describes a TFT structure having a shottky barrier that includes a silicon film 12, which the Examiner equates to the recited semiconductor layer, on which is formed a titanium silicide film 15, which the Examiner equates to the recited side recess. Applicants submit, however, that titanium silicide film 15 is a film and, therefore, is not a recess. Moreover, even if, for the sake of argument, the portion of the silicon film 12 on which the titanium silicide film 15 is formed were somehow construed as a recess, applicants submit that this recess would not be a "side" recess, as claimed.

For at least this reason, applicants request reconsideration and withdrawal of the rejection of claims 20, 34, 41 and 49, and their dependent claims.

Each of claims 41 and 49, as amended, recites a source electrode that contains a first layer and a second layer, wherein a part of each of the first and second layers is located over an interlayer insulating film. Titanium silicide film 15, which the Examiner also equates to the recited first layer, is not located over an interlayer insulating film. Rather, it is located over

silicon film 12. For at least this additional reason, applicants request reconsideration and withdrawal of the rejection of claims 41 and 49, and their dependent claims.

Applicants also note that in rejecting claims 34 and 49, the Examiner equates the recited fourth layer with "the wiring connected to layer 125, see figures 11A and 11B." Applicants, however, are unable to identify the wiring referred to by the Examiner in figures 11A and 11B. Applicants respectfully request that the Examiner specifically point out which element shown in these figures is being equated by the Examiner with the recited wiring.

Dependent claims 29, 36, 43 and 51, have been rejected as being unpatentable over Kudoh in view of Aratani (U.S. Patent No. 5,854,139); dependent claims 33, 40, 48, and 56 have been rejected as being unpatentable over Kudoh in view of Applicant's Admitted Prior Art (AAPA), and dependent claims 30, 37, 44 and 52 have been rejected as being unpatentable over Kudoh in view of Tanaka (U.S. Patent No. 5,798,744). Aratani, AAPA, and Tanaka, alone or in combination, do not remedy the failure of Kudoh to describe or suggest the above features, and, therefore, applicants request reconsideration and withdrawal of the rejections of claims 29, 30, 33, 36, 37, 40, 43, 44, 48, 51, 52 and 56.

Applicants submit that all claims are in condition for allowance.

The fees in the amount of \$810 for Request for Continued Examination are being paid concurrently herewith on the Electronic Filing System (EFS) by way of Deposit Account authorization. Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,



Roberto J. Devoto
Reg. No. 55,108

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Fish & Richardson P.C.
1425 K Street, N.W.
11th Floor
Washington, DC 20005-3500
Telephone: (202) 783-5070
Facsimile: (202) 783-2331